

Title (en)

Layered structure and method to produce such a layered structure

Title (de)

Schichtstruktur und Verfahren zur Herstellung einer Schichtstruktur

Title (fr)

Structure stratifiée et procédé de fabrication de la structure stratifiée

Publication

EP 1475567 A1 20041110 (DE)

Application

EP 03010387 A 20030508

Priority

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Abstract (en)

The laminated structure (1) consists of a underlayer (4), an at least partially porous intermediate layer (7) on the underlayer, and an at least partially sealed outer layer (13). The intermediate layer and underlayer are metal or ceramic. The intermediate layer may be in foam or sponge form. The outer layer is ceramic and especially a heat insulating layer. The underlayer has cooling passages (16) through which a cooling medium through the underlayer can reach the porous intermediate layer. An independent claim is included for a method for the manufacture of a laminated structure.

Abstract (de)

Schichtstrukturen nach dem Stand der Technik weisen eine nicht so effiziente Kühlung gegen ein äußeres heißes Gas auf. Die erfindungsgemäß ausgebildete Schichtstruktur (1) weist neben einer porösen Zwischenschicht (7) eine zumindest teilweise dichte Außenschicht (13) auf. Somit kann die Kühlung und der Schutz vor zu hohem Wärmeeintrag für die Schichtstruktur (1) verbessert werden. <IMAGE>

IPC 1-7

F23R 3/00; **F01D 5/18**; **F01D 5/28**

IPC 8 full level

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CPC (source: EP)

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